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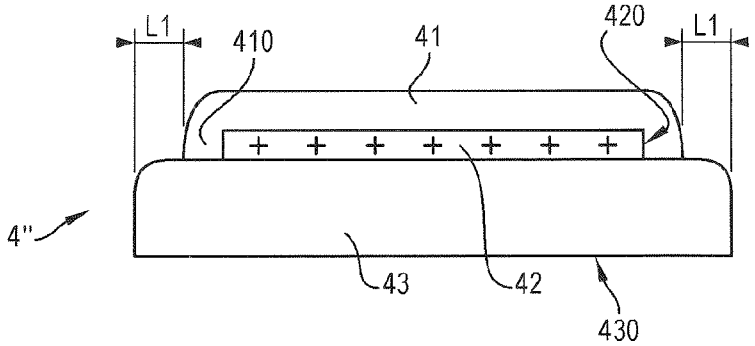
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(54) **Title**: METHOD FOR FINISHING A SUBSTRATE OF THE SEMICONDUCTOR-ON-INSULATOR TYPE

FIG. 6C



(57) **Abstract**: The invention relates to finishing a substrate (4) of the semiconductor-on-insulator (SeOI) type comprising an insulator layer (42) buried between two semiconducting material layers (41, 43). This method is remarkable in that it successively comprises: routing the annular periphery of said substrate (4) so as to obtain a routed substrate (4')/ - encapsulating the routed substrate (4')/ so as to cover the routed side edge (420) of said buried insulator layer (42), by means of a semiconducting material (410).

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